

# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage
- : V<sub>CEO(SUS)</sub> = 400V(Min.)
- · Collector Saturation Voltage
  - :  $V_{CE(sat)} = 1.5 \text{ (Max)} @ I_{C} = 8.0 \text{A}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

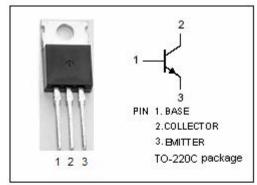
 Designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220V switchmode applications such as switching regulators,inverters,Motor controls,Solenoid/Relay drivers and deflection circuits.

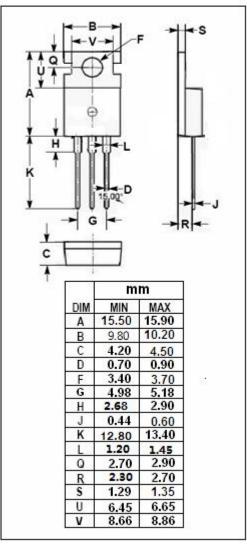
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CEV</sub>	Collector-Emitter Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
Ic	Collector Current-Continuous	12	А
Ісм	Collector Current-peak	24	Α
I <sub>B</sub>	Base Current	6	Α
I <sub>BM</sub>	Base Current-Peak	12	Α
Pc	Collector Power Dissipation T <sub>C</sub> =25°C	100	W
Ti	Junction Temperature		$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range -65~		$^{\circ}$

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.25	°C/W







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**FJP13009** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub> =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	400		V
VcE(sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A ;I <sub>B</sub> = 1A		1.0	V
V <sub>CE</sub> (sat)-2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 1.6A		1.5	V
V <sub>CE(sat)-3</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 12A ;I <sub>B</sub> = 3A		3.0	٧
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A ;I <sub>B</sub> = 1A		1.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 1.6A		1.6	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 700V; I <sub>E</sub> =0		1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 9V; I <sub>C</sub> = 0		1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	8	40	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V	6	30	

### ♦ h<sub>FE-1</sub> Classifications

H1	H2
8-17	15-28

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